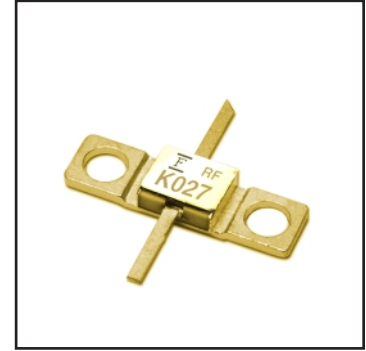


FEATURES

- High Output Power: $P_{1dB} = 24.0\text{dBm(Typ.)}$
- High Gain: $G_{1dB} = 7.0\text{dB(Typ.)}$
- High PAE: $\eta_{add} = 32\%\text{(Typ.)}$
- Proven Reliability
- Hermetic Metal/Ceramic Package

DESCRIPTION

The FLK027WG is a power GaAs FET that is designed for general purpose applications in the Ku-Band frequency range as it provides superior power, gain, and efficiency.



Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ\text{C}$	1.875	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 2.2 and -0.1 mA respectively with gate resistance of 2000 Ω .
3. The operating channel temperature (T_{ch}) should not exceed 145 $^\circ\text{C}$.

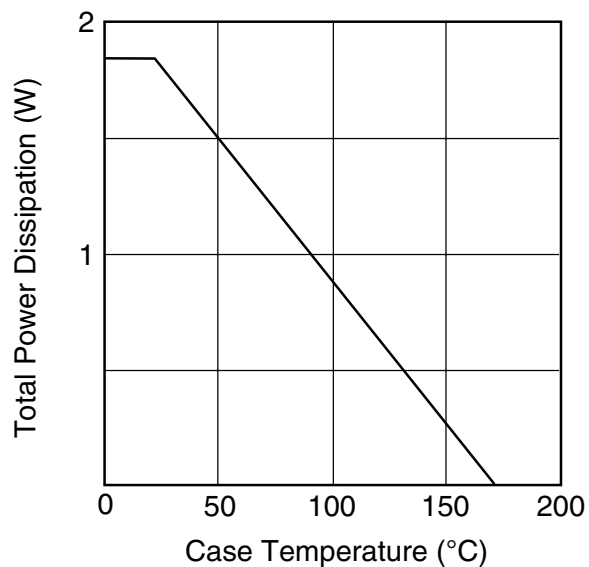
ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	100	150	mA
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 65\text{mA}$	-	50	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 5\text{mA}$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -5\mu\text{A}$	-5	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.6 I_{DSS} \text{ (Typ.)},$ $f = 14.5 \text{ GHz}$	23.0	24.0	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		6.0	7.0	-	dB
Power-added Efficiency	η_{add}		-	32	-	%
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.6 I_{DSS} \text{ (Typ.)},$ $f = 12 \text{ GHz}$	-	24	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		-	8	-	dB
Power-added Efficiency	η_{add}		-	34	-	%
Thermal Resistance	R_{th}	Channel to Case	-	40	80	$^\circ\text{C/W}$

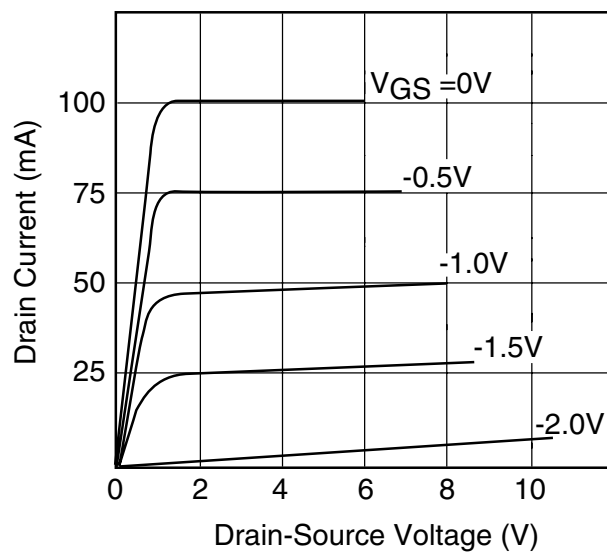
CASE STYLE: WG

G.C.P.: Gain Compression Point

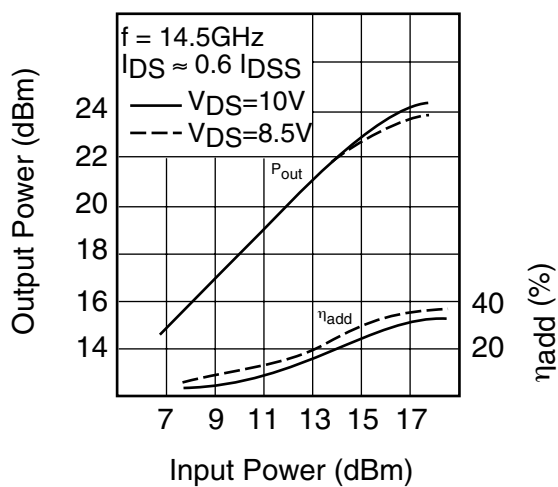
POWER DERATING CURVE



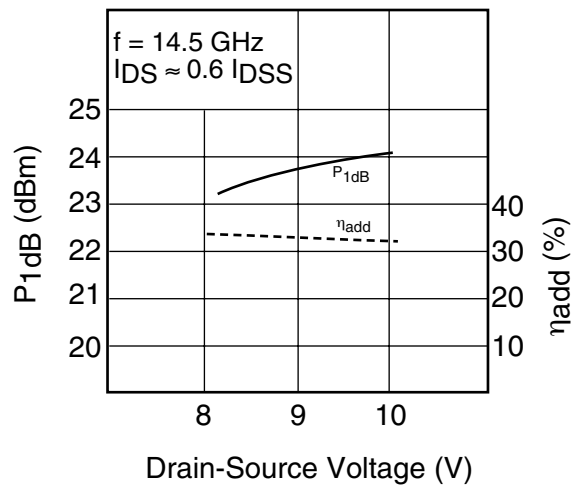
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE

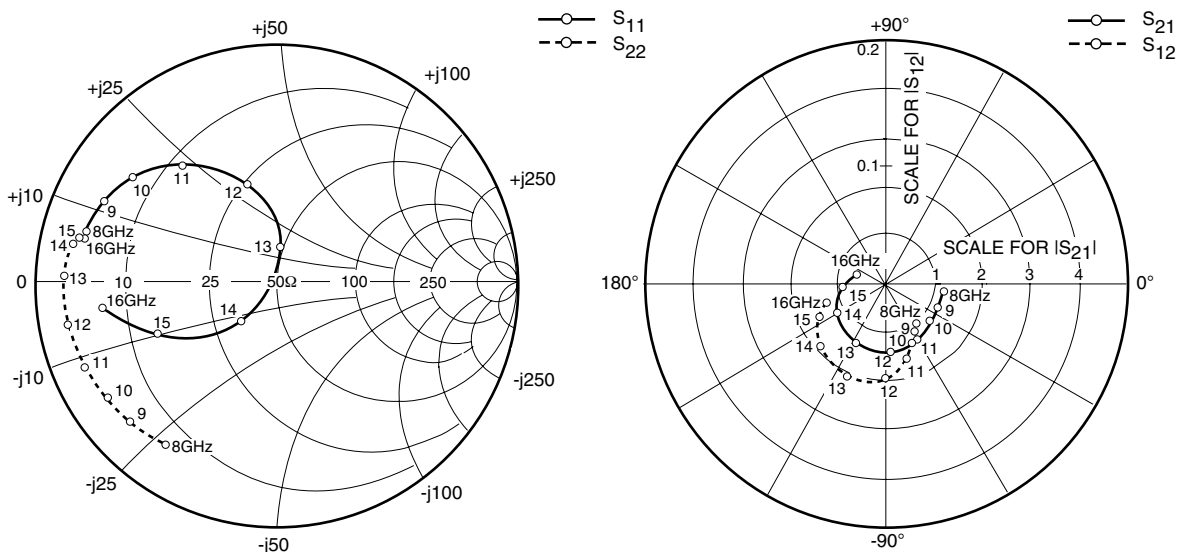


OUTPUT POWER vs. INPUT POWER



P_{1dB} & η_{add} vs. V_{DS}





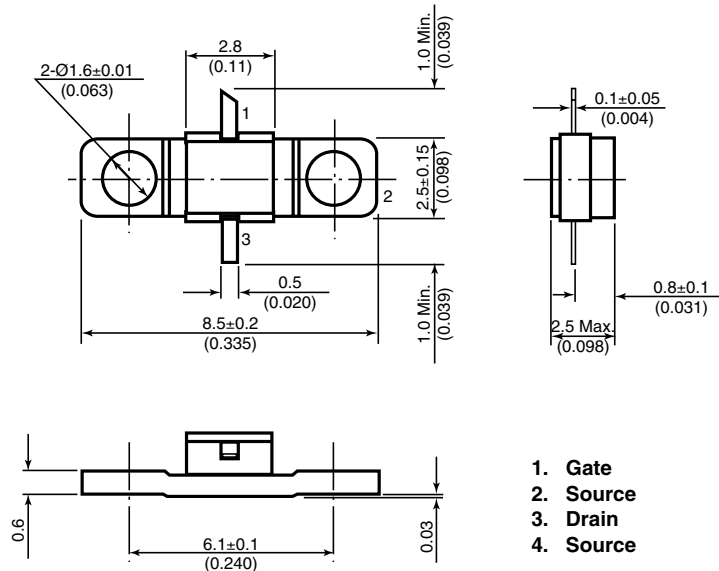
S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 60mA$

FREQUENCY (MHZ)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
500	.985	-31.8	4.381	156.3	.011	67.8	.758	-13.7
1000	.965	-60.1	3.965	134.7	.021	48.5	.748	-27.2
8000	.819	165.4	1.204	-8.3	.041	-54.3	.825	-123.9
8500	.804	159.8	1.177	-16.6	.043	-56.1	.832	-130.0
9000	.787	155.0	1.161	-24.5	.046	-58.6	.838	-135.6
9500	.766	150.1	1.164	-32.1	.049	-61.0	.842	-140.2
10000	.735	144.2	1.197	-40.4	.053	-63.6	.853	-144.8
10500	.689	137.4	1.248	-49.7	.058	-68.7	.864	-149.6
11000	.623	128.7	1.309	-60.3	.065	-74.0	.871	-155.0
11500	.534	118.5	1.364	-72.9	.072	-81.9	.878	-161.4
12000	.423	106.5	1.407	-86.4	.078	-90.5	.885	-167.8
12500	.290	93.9	1.413	-101.2	.082	-101.5	.886	-174.6
13000	.139	82.0	1.380	-116.8	.083	-112.3	.882	178.7
13500	.036	-123.8	1.304	-133.2	.080	-123.7	.875	173.0
14000	.223	-131.8	1.190	-149.4	.075	-136.1	.861	169.2
14500	.395	-144.2	1.041	-164.5	.068	-145.6	.849	167.8
15000	.542	-155.7	.893	-177.4	.061	-152.8	.842	167.4
15500	.652	-164.2	.757	172.1	.054	-156.1	.832	167.6
16000	.734	-170.9	.655	163.3	.052	-160.8	.829	167.3

Case Style "WG"

Metal-Ceramic Hermetic Package



Unit: mm(inches)

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- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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